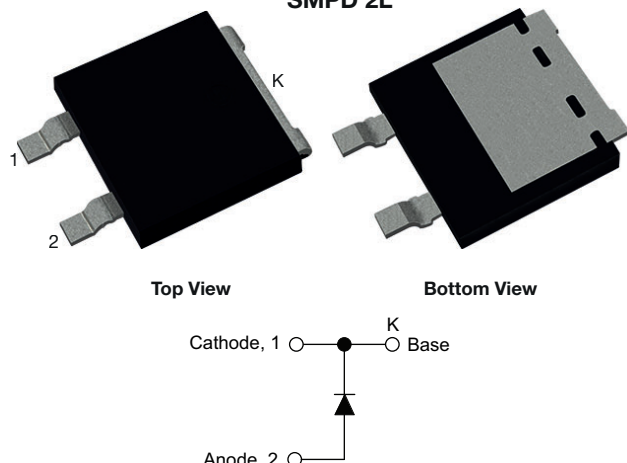


650 V Power SiC Gen 3 Merged PIN Schottky Diode, 10 A

eSMP® Series SMPD 2L



FEATURES

- Creepage and clearance distance 3.6 mm minimum
- Very low profile – typical height of 1.7mm
- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V_F and efficiency by thin wafer technology
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: SMPD 2L

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS	
I_F	10 A
V_R	650 V
V_F at I_F at 25 °C, typ.	1.30 V
T_J max.	175 °C
I_R at V_R at 175 °C	19 μ A
Q_C ($V_R = 400$ V)	29 nC
Package	SMPD 2L
Circuit configuration	Single

MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise specified)				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		650	V
Continuous forward current	I_F	$T_M = 147$ °C (DC)	10	A
DC blocking voltage	V_{DC}		650	V
Repetitive peak surge current	I_{FRM}	$T_M = 25$ °C, $f = 50$ Hz, square wave, DC = 25 %	49	A
Non-repetitive peak forward surge current	I_{FSM}	$T_M = 25$ °C, $t_p = 10$ ms, half sine wave	60	A
		$T_M = 110$ °C, $t_p = 10$ ms, half sine wave	58	
Power dissipation	$P_{tot}^{(1)}$	$T_M = 25$ °C	81	W
		$T_M = 110$ °C	35	
	$P_{tot}^{(2)}$	$T_M = 25$ °C	106	W
		$T_M = 110$ °C	46	
I^2t value	$\int i^2 dt$	$T_M = 25$ °C	18	A ² s
		$T_M = 110$ °C	17	
Operating junction and storage temperatures	$T_J^{(3)}, T_{Stg}$		-55 to +175	°C

Notes

(1) Based on maximum R_{th}

(2) Based on typical R_{th}

(3) The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{thJA}$

**ELECTRICAL SPECIFICATIONS** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Forward voltage	V_F	$I_F = 10\text{ A}$	-	1.3	1.5	V
		$I_F = 10\text{ A}, T_J = 150^\circ\text{C}$	-	1.46	1.85	
		$I_F = 10\text{ A}, T_J = 175^\circ\text{C}$	-	1.52	-	
Reverse leakage current	I_R	$V_R = V_R \text{ rated}$	-	0.7	55	μA
		$V_R = V_R \text{ rated}, T_J = 150^\circ\text{C}$	-	11	125	
		$V_R = V_R \text{ rated}, T_J = 175^\circ\text{C}$	-	19	-	
Total capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}$	-	445	-	pF
		$V_R = 400\text{ V}, f = 1\text{ MHz}$	-	43	-	
Total capacitive charge	Q_C	$V_R = 400\text{ V}, f = 1\text{ MHz}$	-	29	-	nC

THERMAL - MECHANICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-mount	R_{thJM}		-	1.4	1.8	$^\circ\text{C/W}$
Marking device				3C10ED07T		

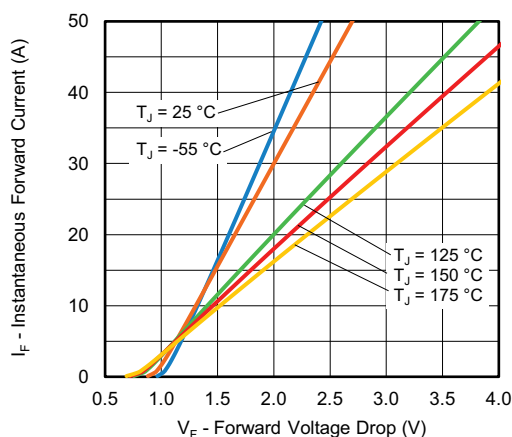


Fig. 1 - Typical Forward Voltage Drop Characteristics

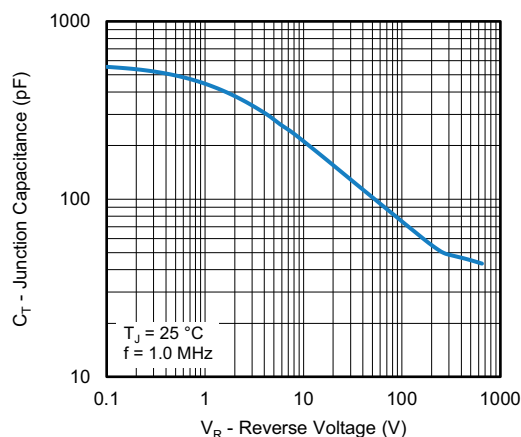


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

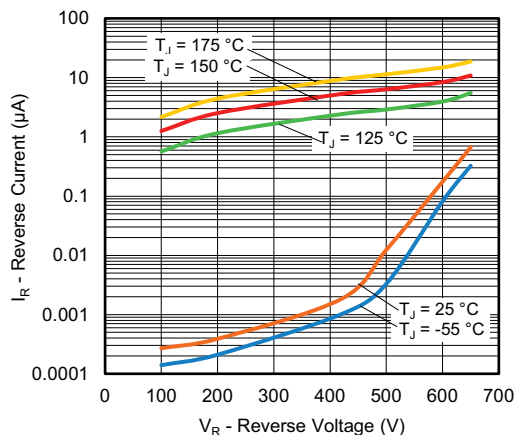


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

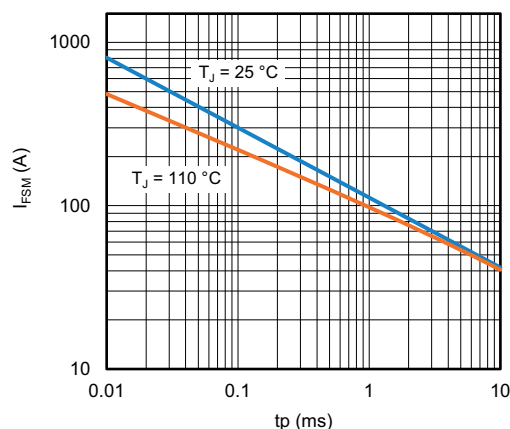


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

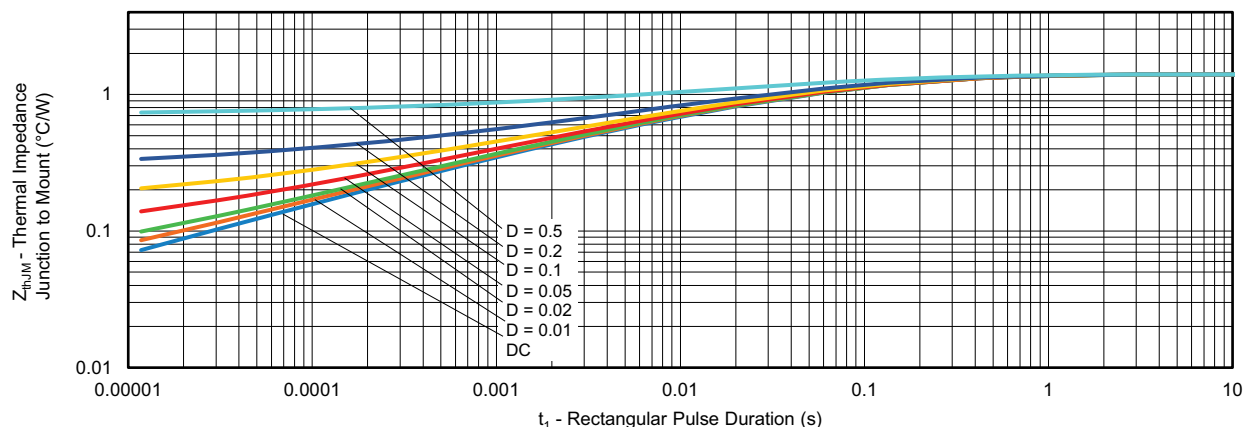
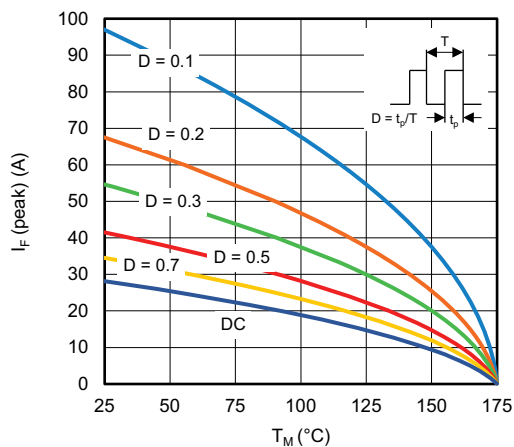

Fig. 5 - Typical Thermal Impedance Z_{thJM} Characteristics


Fig. 6 - Peak Forward Current vs. Maximum Allowable Mount Temperature

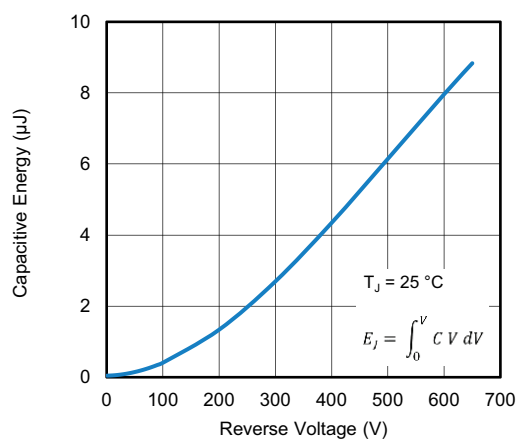


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

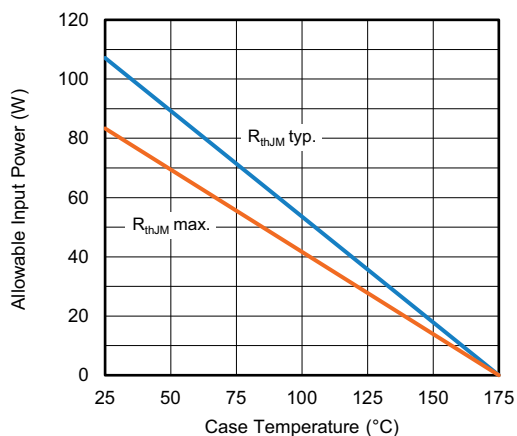


Fig. 7 - Forward Power Loss Characteristics

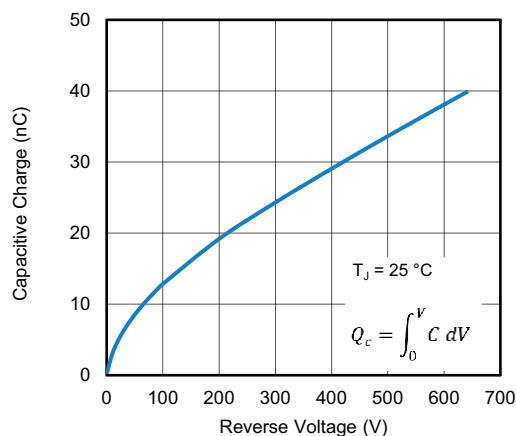


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



ORDERING INFORMATION TABLE

Device code	VS-	3C	10	E	D	07	T	-M3
	1	2	3	4	5	6	7	8

1	-	Vishay Semiconductors product
2	-	3C = SiC diode, Generation 3
3	-	Current rating (10 = 10 A)
4	-	E = single diode
5	-	Package SMPD 2L
6	-	Voltage rating: (07 = 650 V)
7	-	T = true 2 pin
8	-	Environmental digit: -M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION				
ORDERING P/N	UNIT WEIGHT	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
VS-3C10ED07T-M3/I	0.52 g	I	2000/reel	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?97059
Part marking information	www.vishay.com/doc?97105
Packaging information	www.vishay.com/doc?88869



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